

MITSUBISHI SEMICONDUCTOR &lt;INTELLIGENT POWER MODULES&gt;

# PM50CTJ060-3

INSULATED PACKAGE  
FLAT-BASE TYPE

## PM50CTJ060-3



- 4th gen. planer IGBTs are integrated
- 3φ 50A, 600V Current-sense IGBT type inverter
- Monolithic gate drive & protection logic
- Detection, protection & status indication circuits for over-current, short-circuit, over-temperature & under-voltage
- Acoustic noise-less 3.7kW class inverter application

## APPLICATION

Air-conditioner, General purpose inverter, servo drives and other motor controls

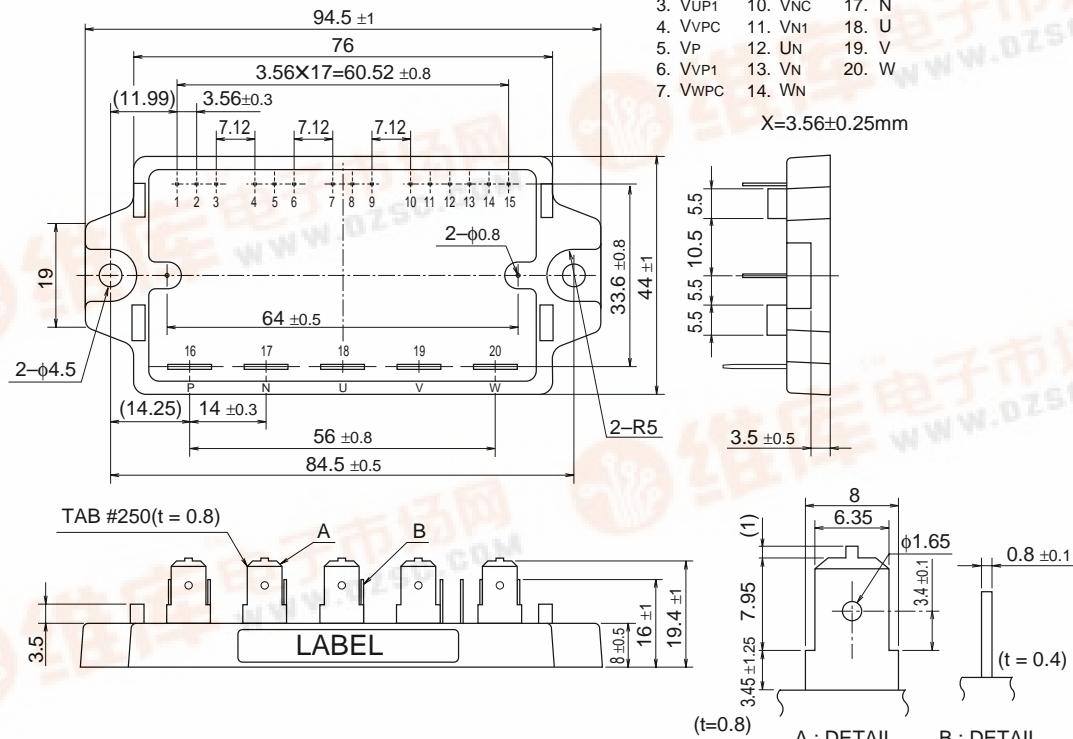
### OUTLINE DRAWING

Dimensions in mm

## Terminal code

1. VUPC	8. VP	15. FO
2. UP	9. VWP1	16. P
3. VUP1	10. VNC	17. N
4. VVPC	11. VN1	18. U
5. VP	12. UN	19. V
6. VVP1	13. VN	20. W
7. VVPC	14. WN	

$$X=3.56\pm 0.25\text{mm}$$

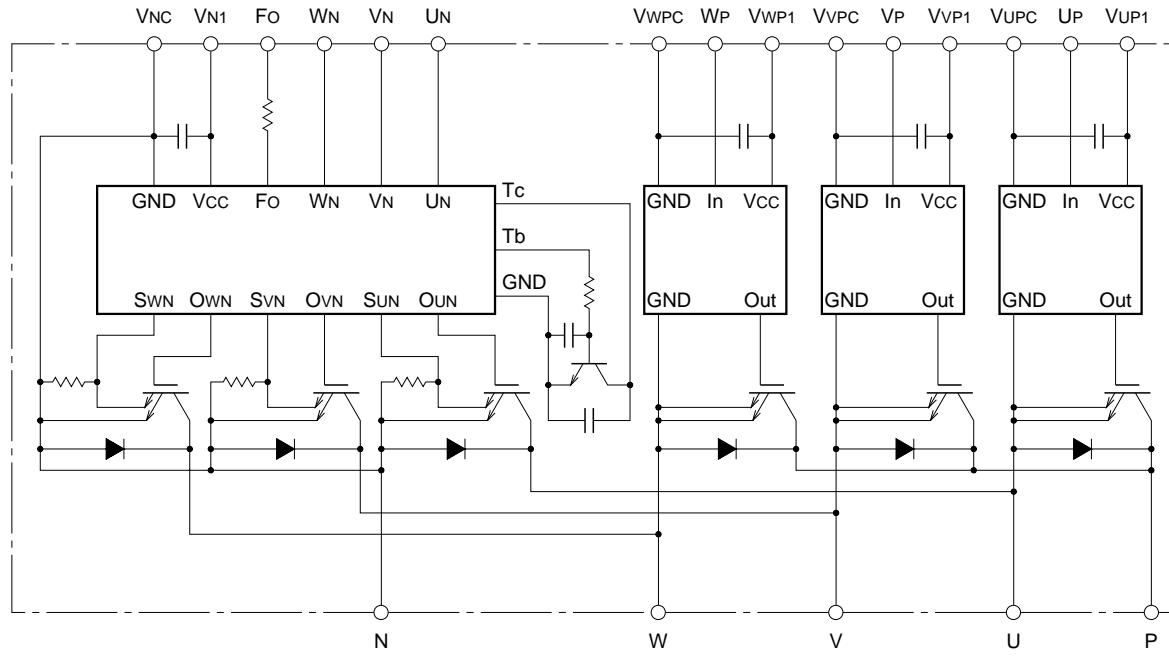


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**EQUIVALENT CIRCUIT DIAGRAM**



**MAXIMUM RATINGS** ( $T_j = 25^\circ\text{C}$ , unless otherwise noted)

**INVERTER PART**

Symbol	Parameter	Conditions	Ratings	Unit
Vcc	Supply voltage	Applied between : P-N	450	V
VCC(surge)	Supply voltage (surge)	Applied between : P-N, Surge value	500	V
VCES	Collector-emitter voltage		600	V
$\pm I_C$	Collector current	$T_c = 25^\circ\text{C}$	50	A
$\pm I_{CP}$	Collector current (peak)	$T_c = 25^\circ\text{C}$	100	A
Pc	Collector dissipation	$T_c = 25^\circ\text{C}$	100	W
$T_j$	Junction temperature		-20 ~ +125*	$^\circ\text{C}$

\* The item defines the maximum junction temperature for the power elements (IGBT/Diode) of the IPM to ensure safe operation. However, these power elements can endure junction temperature as high as  $150^\circ\text{C}$  instantaneously. To make use of this additional temperature allowance, a detailed study of the exact application conditions is required and, accordingly, necessary information is requested to be provided before use.

**CONTROL PART**

Symbol	Parameter	Conditions	Ratings	Unit
Vd	Supply voltage	Applied between : VUP1-VUPC, VVP1-VVPC VWP1-VWPC, VN1-VNC	20	V
Icin	Input current	At : UP, VP, WP, UN, VN, WN terminals	20	mA
Vfo	Fault output supply voltage	Applied between : Fo-VNC	20	V
ifo	Fault output current	Sink current of Fo terminals	20	mA

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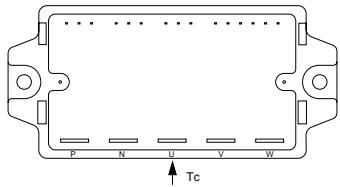
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**TOTAL SYSTEM**

Symbol	Parameter	Conditions	Ratings	Unit
V <sub>CC(PROT)</sub>	Supply voltage protected by OC & SC	V <sub>D</sub> = 13.5 ~ 16.5V, Inverter part, T <sub>j</sub> = 125°C start	400	V
T <sub>C</sub>	Module case operating temperature	(Note 1)	-20 ~ +100	°C
T <sub>STG</sub>	Storage temperature		-40 ~ +125	°C
V <sub>ISO</sub>	Isolation voltage	60Hz, sinusoidal, Charged part to Base, AC · 1 min.	2500	V <sub>rms</sub>

Note 1 : T<sub>C</sub> measurement point.



**THERMAL RESISTANCES**

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
R <sub>th(j-c)Q</sub>	Junction to case thermal resistances	Inverter IGBT part (per 1/6 module)	—	—	1.2	°C / W
R <sub>th(j-c)F</sub>		Inverter FWD part (per 1/6 module)	—	—	2.9	°C / W
R <sub>th(c-f)</sub>	Contact thermal resistance	Case to fin, (per 1 module) thermal grease applied	—	—	0.4	°C / W

**ELECTRICAL CHARACTERISTICS (T<sub>j</sub> = 25°C, unless otherwise noted)**

**INVERTER PART**

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	V <sub>D</sub> = 15V, I <sub>CIN</sub> = 10mA I <sub>C</sub> = 50A, Pulsed (Fig. 1)	—	1.8	2.6	V
		T <sub>j</sub> = 25°C T <sub>j</sub> = 125°C	—	2.0	3.0	
V <sub>EC</sub>	FWD forward voltage	—I <sub>C</sub> = 50A, V <sub>D</sub> = 15V, I <sub>CIN</sub> = 0mA (Fig. 2)	—	2.5	3.5	V
t <sub>on</sub>	Switching time	V <sub>D</sub> = 15V, I <sub>CIN</sub> = 0mA → 10mA V <sub>CC</sub> = 300V, I <sub>C</sub> = 50A T <sub>j</sub> = 125°C Inductive Load (Upper-Lower Arm) (Fig. 3)	0.5	1.0	2.0	μs
t <sub>rr</sub>			—	0.1	—	μs
t <sub>c(on)</sub>			—	0.3	0.9	μs
t <sub>off</sub>			—	3.0	4.0	μs
t <sub>c(off)</sub>			—	1.0	2.0	μs
I <sub>CES</sub>	Collector-emitter cutoff current	V <sub>CE</sub> = V <sub>CES</sub> , V <sub>D</sub> = 15V (Fig. 4)	—	—	1	mA
		T <sub>j</sub> = 25°C T <sub>j</sub> = 125°C	—	—	10	

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**CONTROL PART**

Symbol	Parameter	Test conditions	Limits			Unit	
			Min.	Typ.	Max.		
ID	Circuit current	VD = 15V, ICIN = 0mA	VN1-VNC	—	25	35	
			VXP1-VXPC	—	5	10	
Ith(ON)	Input on threshold current	At : UP-VUPC, VP-VVPC, WP-VWPC UN · VN · WN-VNC terminals		1	3	5 mA	
Ith(OFF)	Input off threshold current			1	3	5 mA	
OC	Over current trip level	-20°C ≤ Tj ≤ 125°C, VD = 15V (Fig. 5, 6) (Lower Arm only)		65	91	— A	
SC	Short circuit trip level	-20°C ≤ Tj ≤ 125°C, VD = 15V (Fig. 5, 6) (Lower Arm only)		—	130	— A	
tOFF(OC)	Over current delay time	VD = 15V (Fig. 5, 6)		—	10	— μs	
OT	Over temperature protection	Baseplate	Trip level	100	110	120 °C	
		Temperature detection, VD = 15V	Reset level	—	90	— °C	
UV	Supply circuit under voltage protection	-20°C ≤ Tj ≤ 125°C (Lower Arm only)	Trip level	11.5	12.0	12.5 V	
			Reset level	—	12.5	— V	
IFO(H)	Fault output current	VD = 15V, VFO = 15V		(Note 2)	—	0.01 mA	
IFO(L)					—	10 mA	
tFO	Minimum fault output pulse width	VD = 15V		(Note 2)	1.0	1.8 ms	

Note 2 : Fault output is given only when the internal OC, SC, OT & UV protections schemes of lower arm device operate to protect it.

**MECHANICAL RATINGS AND CHARACTERISTICS**

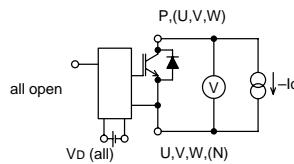
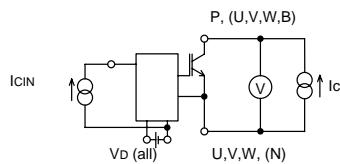
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
—	Mounting torque	Mounting part screw : M4	0.98	1.18	1.47	N·m
—	Weight		—	80	—	g

**RECOMMENDED CONDITIONS FOR USE**

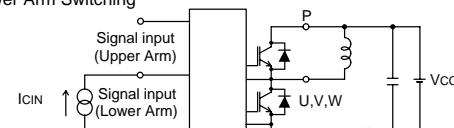
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
VCC	Supply voltage	Applied across P-N terminals	0	300	400	V
		Applied between : VUP1-VUPC, VVP1-VVPC VWP1-VWPC, VN1-VNC	13.5	15.0	16.5	V
ICIN(ON)	Input on current	At : UP, VP, WP, UN, VN, WN terminals	5	10	20	mA
ICIN(OFF)	Input off current		0	—	1	mA
fPWM	PWM input frequency	For IPM's each input signals, (Fig. 7)	—	—	8	kHz
tdead	Arm shoot-through blocking time	For IPM's each input signals, (Fig. 7)	3.5	—	—	μs

## PRECAUTIONS FOR TESTING

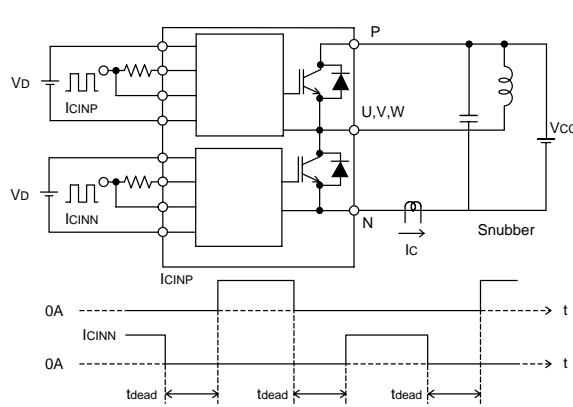
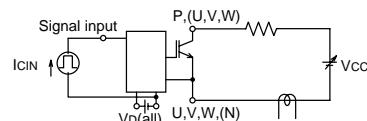
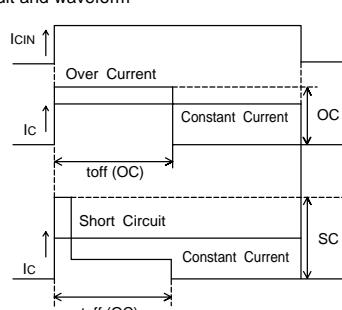
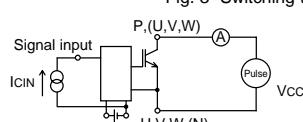
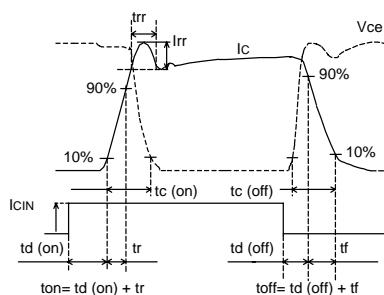
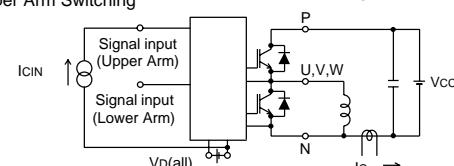
- Before applying any control supply voltage ( $V_D$ ), the input signals should be turned on from its off state.  
After this, the specified ON and OFF level setting for each input signal should be done.
- When performing "OC" and "SC" tests, the turn-off surge voltage spike at the corresponding protection operation should not be allowed to rise above  $V_{CES}$  rating of the device.  
(These test should not be done by using a curve tracer or its equivalent.)



a) Lower Arm Switching



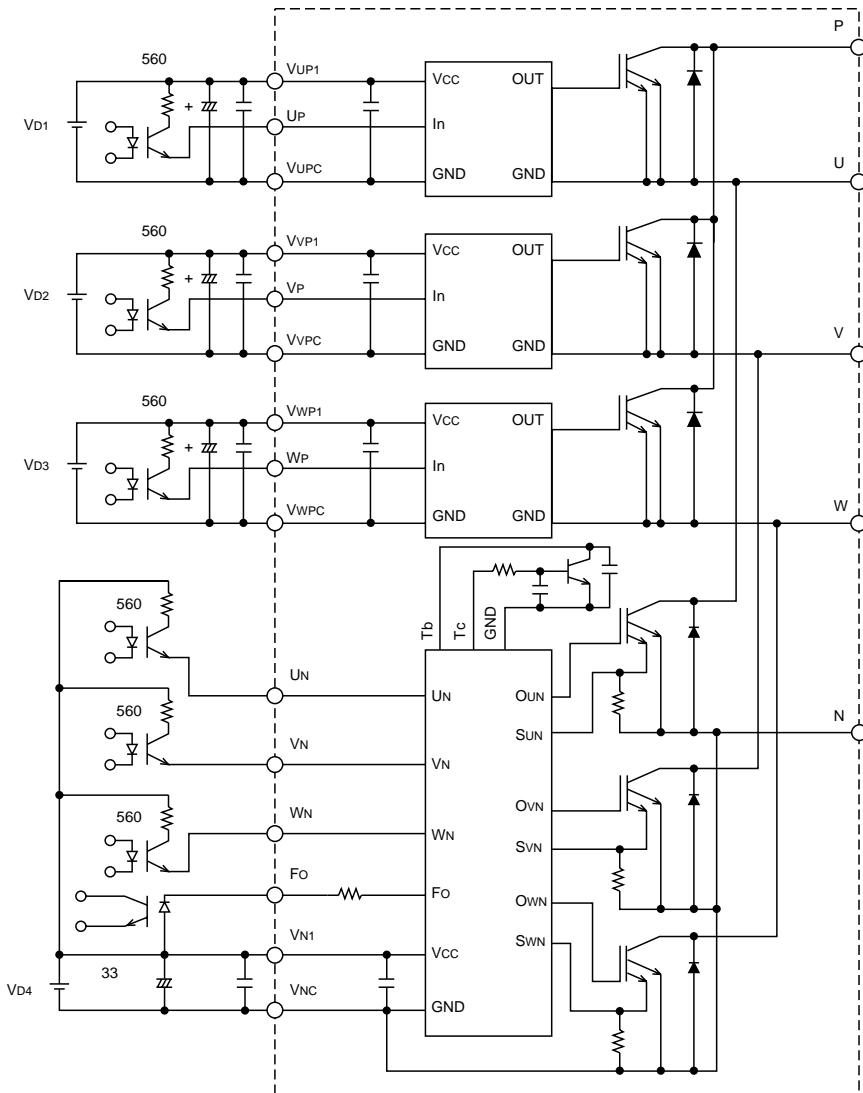
b) Upper Arm Switching



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**NOTES FOR STABLE AND SAFE OPERATION :**

- Design the PCB pattern to minimize wiring length between opto-coupler and IPM's input terminal, and also to minimize the stray capacity between the input and output wirings of opto-coupler.
- Connect low impedance capacitor between the Vcc and GND terminal of each switching opto-coupler.
- Slow switching opto-coupler : CTR = 100%~200%
- Use 4 isolated control power supplies (Vd). Also, care should be taken to minimize the instantaneous voltage charge of the power supply.
- Make inductance of DC bus line as small as possible, and minimize surge voltage using snubber capacitor between P and N terminal.
- Use line noise filter capacitor (ex. 4.7nF) between each input AC line and ground to reject common-mode noise from AC line and improve noise immunity of the system.